

PSMN1R8-30BL

N-channel 30 V, 1.8 m Ω logic level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product of

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	270	W
junction temperature			-55	-	175	°C
acteristics						
drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>		-	2.17	2.6	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>		-	1.55	1.8	mΩ
haracteristics						
gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$		-	22	-	nC
total gate charge	see Figure 14; see Figure 15		-	83	-	nC
ruggedness						
non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 30 V; R_{GS} = 50 Ω ; unclamped		-	-	1.1	J
	drain-source voltage drain current total power dissipation junction temperature cacteristics drain-source on-state resistance haracteristics gate-drain charge total gate charge ruggedness non-repetitive drain-source	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ junction temperature acteristics drain-source on-state resistance $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 100 ^{\circ}\text{C};$ see Figure 13; see Figure 12 $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12 haracteristics gate-drain charge $V_{GS} = 4.5 \text{V}; I_D = 25 \text{A}; V_{DS} = 15 \text{V};$ total gate charge $V_{GS} = 4.5 \text{V}; I_D = 25 \text{A}; V_{DS} = 15 \text{V};$ see Figure 14; see Figure 15 ruggedness non-repetitive drain-source $V_{GS} = 10 \text{V}; T_{j(init)} = 25 ^{\circ}\text{C}; I_D = 100 \text{A};$	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ junction temperature acteristics drain-source on-state $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 100 ^{\circ}\text{C};$ see Figure 13; see Figure 12 $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12 haracteristics gate-drain charge $V_{GS} = 4.5 \text{V}; I_D = 25 \text{A}; V_{DS} = 15 \text{V};$ total gate charge $V_{GS} = 10 \text{V}; T_{j(init)} = 25 ^{\circ}\text{C}; T_{j} = 100 \text{A};$	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ - drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1 - see Figure 2 - junction temperature -55 drain-source on-state resistance $V_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 100 ^{\circ}\text{C};$ - see Figure 12 - see Figure 13; see Figure 12 - see Figure 12 - v_{GS} = 10 \text{V}; I_D = 25 \text{A}; T_j = 25 ^{\circ}\text{C}; - see Figure 12 - see Figure 14; see Figure 15 -	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ [1] see Figure 1 junction temperature	$ \begin{array}{c} \text{drain-source voltage} & T_j \geq 25 \text{ °C; } T_j \leq 175 \text{ °C} & - & - & 30 \\ \text{drain current} & T_{mb} = 25 \text{ °C; } V_{GS} = 10 \text{ V;} & 11 & - & - & 100 \\ \text{see Figure 1} & - & - & 270 \\ \text{total power dissipation} & T_{mb} = 25 \text{ °C; see Figure 2} & - & - & 270 \\ \text{junction temperature} & -55 & - & 175 \\ \hline \textbf{acteristics} & & & & & & & & & \\ \text{drain-source on-state resistance} & V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 100 \text{ °C;} & - & 2.17 & 2.6 \\ \hline \textbf{see Figure 13; see Figure 12} & & & & & & & \\ \hline \textbf{V}_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 25 \text{ °C;} & - & 1.55 & 1.8 \\ \hline \textbf{see Figure 12} & & & & & & & & \\ \hline \textbf{bharacteristics} & & & & & & & & \\ \hline \textbf{gate-drain charge} & V_{GS} = 4.5 \text{ V; } I_D = 25 \text{ A; } V_{DS} = 15 \text{ V;} & - & 22 & - \\ \hline \textbf{total gate charge} & & & & & & & & & \\ \hline \textbf{ruggedness} & & & & & & & & \\ \hline \textbf{non-repetitive drain-source} & V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 100 \text{ A;} & - & - & 1.1 \\ \hline \end{array} $

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

		<u> </u>		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R8-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R8-30BL	PSMN1R8-30BL

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	1120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	270	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1120	Α
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	1.1	J

[1] Continuous current is limited by package.

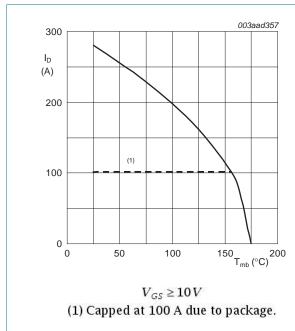
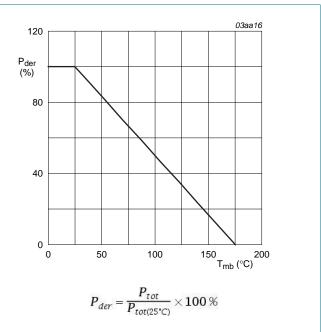


Fig 1. Continuous drain current as a function of mounting base temperature



ig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN1R8-30BL

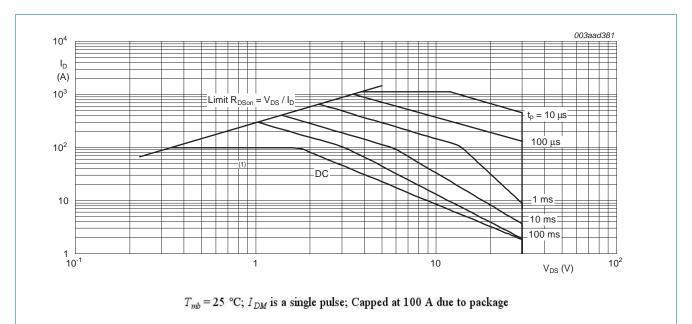


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

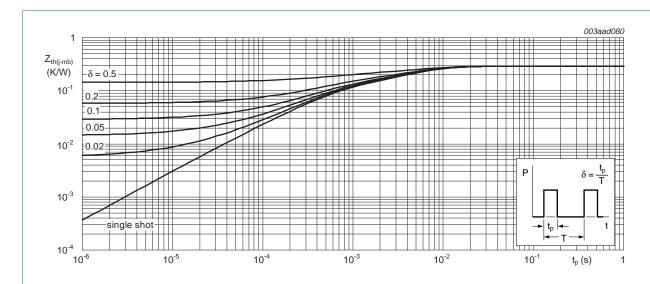


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.3	4	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 125 °C	-	-	200	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon} drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.82	2.1	mΩ	
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 13; see Figure 12	-	2.95	3.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see Figure 13; see Figure 12	-	2.17	2.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.55	1.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	170	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	158	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	83	-	nC
^						
Q_GS	gate-source charge	see Figure 14; see Figure 15	-	29	-	nC
	gate-source charge pre-threshold gate-source charge		-	29 17	-	nC nC
Q _{GS(th)}	pre-threshold gate-source					
$Q_{GS(th)}$ $Q_{GS(th-pl)}$	pre-threshold gate-source charge post-threshold gate-source		-	17		nC
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD}	pre-threshold gate-source charge post-threshold gate-source charge		-	17 12		nC nC
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see Figure 14}; $ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	17 12 22	-	nC nC
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$ C_{iss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure 14}}{\text{Figure 15}};$ see Figure 15	-	17 12 22 2.6	-	nC nC nC V
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$ C_{iss} C_{oss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see Figure 14}; $ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	17 12 22 2.6 10180	-	nC nC nC V
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$ C_{iss} C_{oss} C_{rss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance	see Figure 14; see Figure 15 $I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see Figure 14}; $ see Figure 15 $V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	17 12 22 2.6 10180 2000	- - - -	nC nC v pF pF
$Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $V_{GS(pl)}$ C_{iss} C_{oss} C_{rss}	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance	see Figure 14; see Figure 15 $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 15 \text{ V}$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ °C}$; see Figure 16	-	17 12 22 2.6 10180 2000 872	- - - -	nC nC V pF pF
$\begin{aligned} &Q_{GS}\\ &Q_{GS(th)}\\ &Q_{GS(th-pl)}\\ &Q_{GD}\\ &V_{GS(pl)}\\ &C_{iss}\\ &C_{oss}\\ &C_{rss}\\ &t_{d(on)}\\ &t_{r}\\ &t_{d(off)}\\ \end{aligned}$	pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 14; see Figure 15 $I_D = 25 \text{ A; } V_{DS} = 15 \text{ V; see } \frac{\text{Figure 14;}}{\text{see Figure 15}}$ $V_{DS} = 15 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 16}}{\text{Figure 16}}$ $V_{DS} = 15 \text{ V; } R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V;}$	-	17 12 22 2.6 10180 2000 872 92	- - - - -	nC nC V pF pF pF ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	nin diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 17	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	64	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	60	-	nC

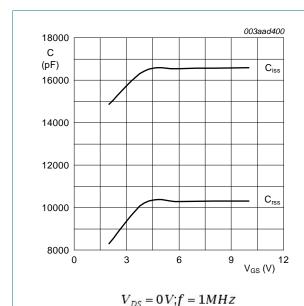


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

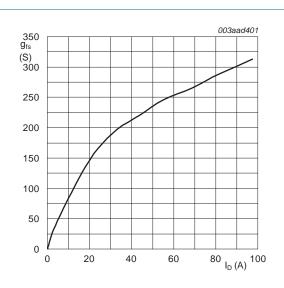


Fig 6. Forward transconductance as a function of

 $T_j = 25 \,^{\circ}C; V_{DS} = 15V$

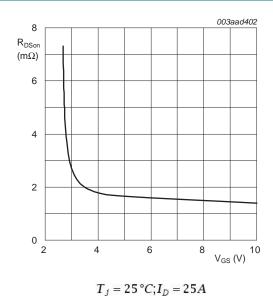


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

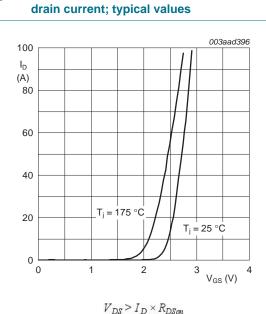


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

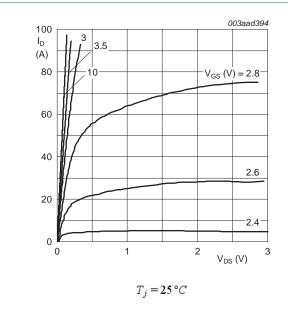


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

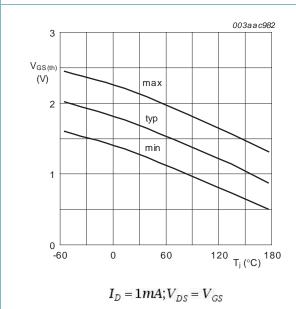
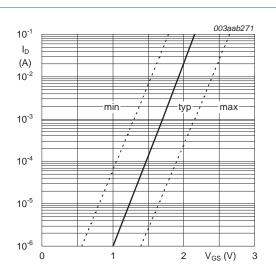


Fig 11. Gate-source threshold voltage as a function of junction temperature



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

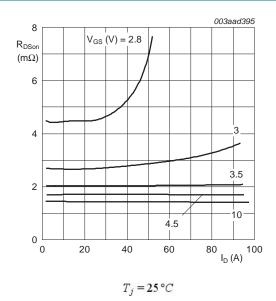


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

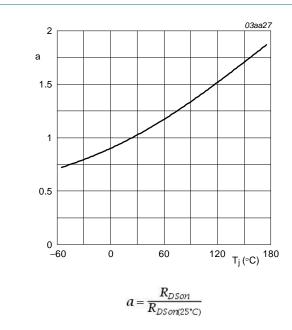


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

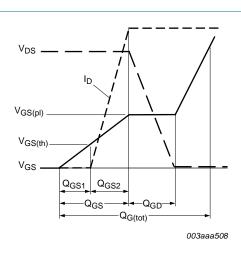


Fig 14. Gate charge waveform definitions

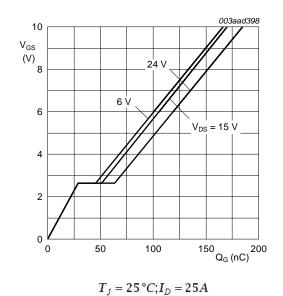
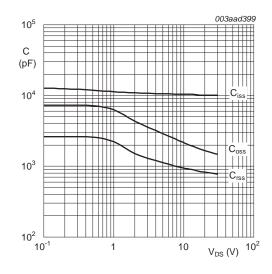
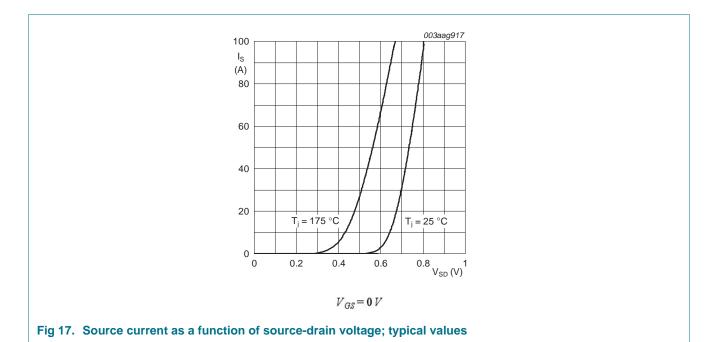


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



8. Package outline

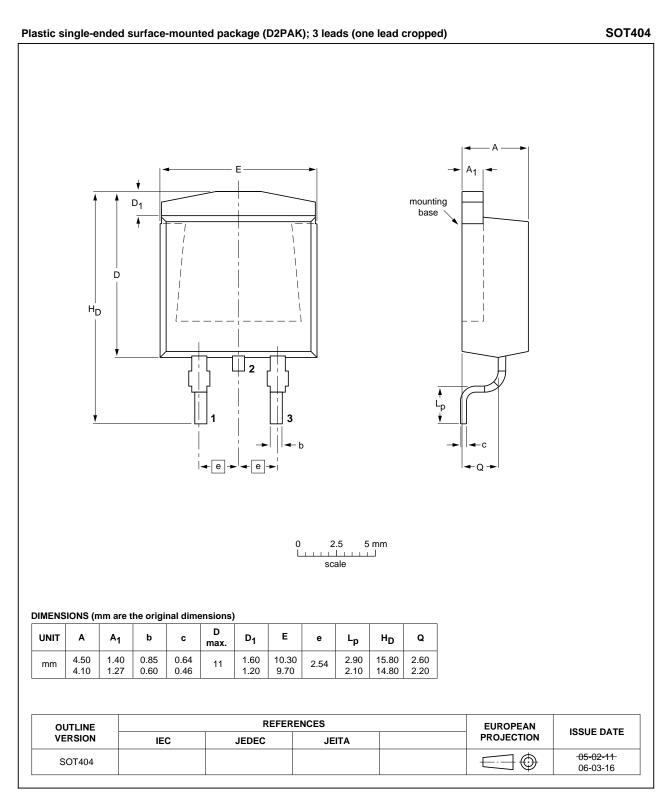


Fig 18. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R8-30BL v.1	20120322	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

10.2 Definitions

Preview — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet

10.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Nexperia takes no responsibility for the content in this document if provided by an information source outside of Nexperia.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia and its suppliers accept no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

PSMN1R8-30BL

All information provided in this document is subject to legal disclaimers.

© Nexperia B.V. 2017. All rights reserved

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective

agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Nexperia product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the

product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

10.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

11. Contact information

For more information, please visit:http://www.nexperia.com

For sales office addresses, please send an email to:salesaddresses@nexperia.com

PSMN1R8-30BL

N-channel 30 V, 1.8 m Ω logic level MOSFET in D2PAK

12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking2
5	Limiting values3
6	Thermal characteristics5
7	Characteristics6
8	Package outline
9	Revision history12
10	Legal information13
10.1	Data sheet status
10.2	Definitions13
10.3	Disclaimers
10.4	Trademarks14
11	Contact information14

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF